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July 2015

FDMS3006SDC

N-Channel Dual Cool™ 56 PowerTrench® SyncFET™ 30 V, 90 A, 1.9 mΩ

Features

- Dual Cool™ Top Side Cooling PQFN package
- Max $r_{DS(on)}$ = 1.9 mΩ at V_{GS} = 10 V, I_D = 30 A
- Max $r_{DS(on)}$ = 2.7 mΩ at V_{GS} = 4.5 V, I_D = 26 A
- High performance technology for extremely low $r_{DS(on)}$
- SyncFET Schottky Body Diode
- RoHS Compliant

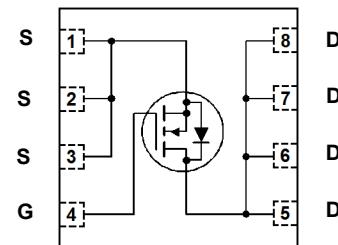
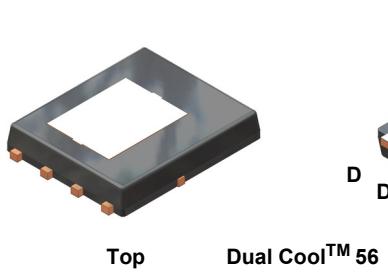


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process. Advancements in both silicon and Dual Cool™ package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Telecom Secondary Side Rectification
- High End Server/Workstation Vcore Low Side



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	(Note 4)	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	90	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	179	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	34	
	-Pulsed	200	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 5)	V/ns
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	89	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	3.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	2.7	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	1.4	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	16	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	23	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	11	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
3006S	FDMS3006SDC	Dual Cool™ 56	13"	12 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	30			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10 \text{ mA}$, referenced to 25°C		16		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			500	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA

On Characteristics

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1 \text{ mA}$	1.2	1.8	3	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 10 \text{ mA}$, referenced to 25°C		-5		$\text{mV}/^\circ\text{C}$
$r_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		1.3	1.9	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 26 \text{ A}$		1.9	2.7	
		$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 125^\circ\text{C}$		1.8	2.7	
g_{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 30 \text{ A}$		176		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		4430	5895	pF
C_{oss}	Output Capacitance			1615	2150	pF
C_{rss}	Reverse Transfer Capacitance			106	160	pF
R_g	Gate Resistance			0.8		Ω

Switching Characteristics

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 30 \text{ A}, V_{GS} = 10 \text{ V}, R_{\text{GEN}} = 6 \Omega$		16	29	ns
t_r	Rise Time			6.3	13	ns
$t_{d(\text{off})}$	Turn-Off Delay Time			40	64	ns
t_f	Fall Time			4.1	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 10 \text{ V}$		61	85	nC
	Total Gate Charge		$V_{DD} = 15 \text{ V}, I_D = 30 \text{ A}$	28	40	nC
Q_{gs}	Gate to Source Gate Charge			12		nC
Q_{gd}	Gate to Drain "Miller" Charge			7		nC

Drain-Source Diode Characteristics

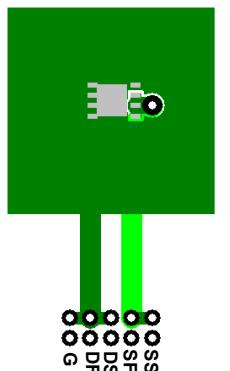
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2 \text{ A}$ (Note 2)		0.4	0.8	V
		$V_{GS} = 0 \text{ V}, I_S = 30 \text{ A}$ (Note 2)		0.8	1.2	
t_{rr}	Reverse Recovery Time	$I_F = 30 \text{ A}, di/dt = 300 \text{ A}/\mu\text{s}$		38	61	ns
				56	90	

Thermal Characteristics

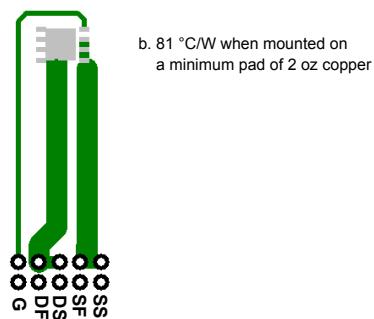
$R_{\theta,JC}$	Thermal Resistance, Junction to Case	(Top Source)	2.7	°C/W
$R_{\theta,JC}$	Thermal Resistance, Junction to Case	(Bottom Drain)	1.4	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	38	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	81	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1c)	27	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1d)	34	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1e)	16	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1f)	19	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1g)	26	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1h)	61	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1i)	16	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1j)	23	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1k)	11	
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient	(Note 1l)	13	

NOTES:

1. $R_{\theta,JA}$ is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.



a. 38 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 81 °C/W when mounted on a minimum pad of 2 oz copper

c. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in² pad of 2 oz copper
d. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
e. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in² pad of 2 oz copper
f. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
g. 200FPM Airflow, No Heat Sink, 1 in² pad of 2 oz copper
h. 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
i. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in² pad of 2 oz copper
j. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
k. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in² pad of 2 oz copper
l. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 µs, Duty cycle < 2.0%.

3. E_{AS} of 144 mJ is based on starting $T_J = 25$ °C, $L = 1$ mH, $I_{AS} = 17$ A, $V_{DD} = 27$ V, $V_{GS} = 10$ V. 100% test at $L = 0.1$ mH, $I_{AS} = 39.2$ A.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

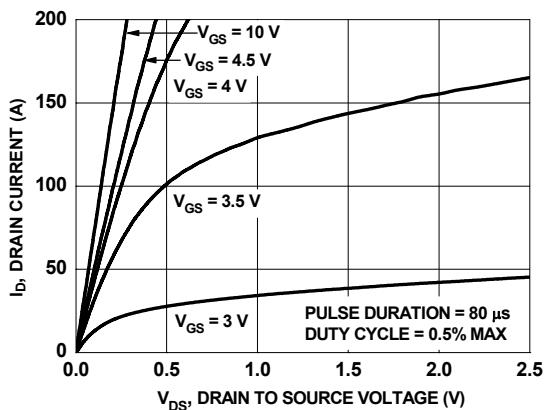


Figure 1. On-Region Characteristics

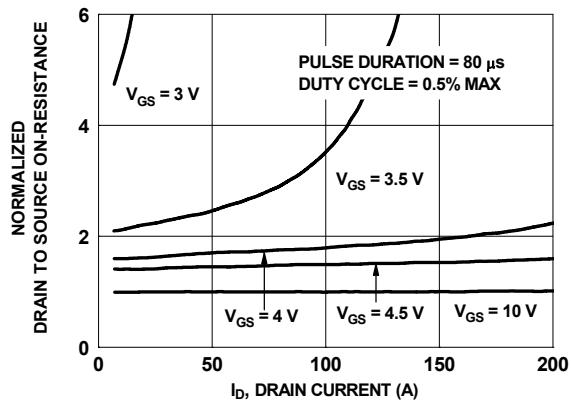


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

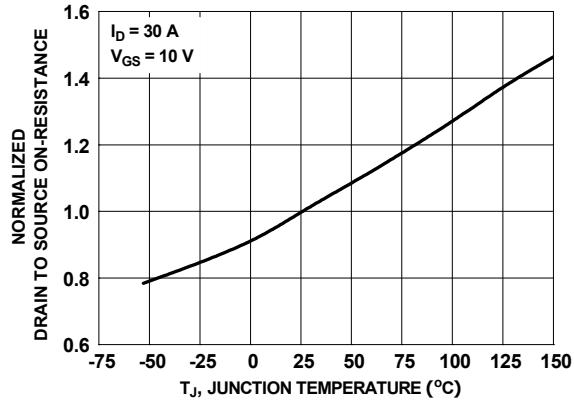


Figure 3. Normalized On-Resistance vs Junction Temperature

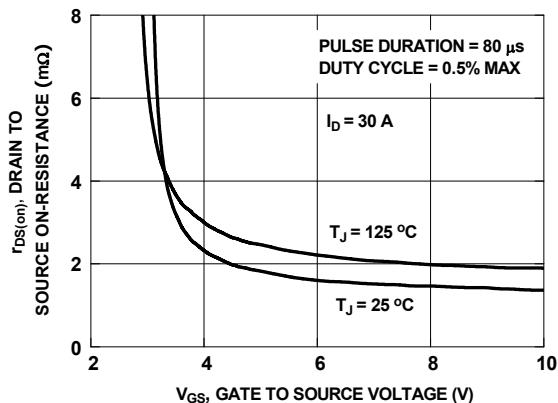


Figure 4. On-Resistance vs Gate to Source Voltage

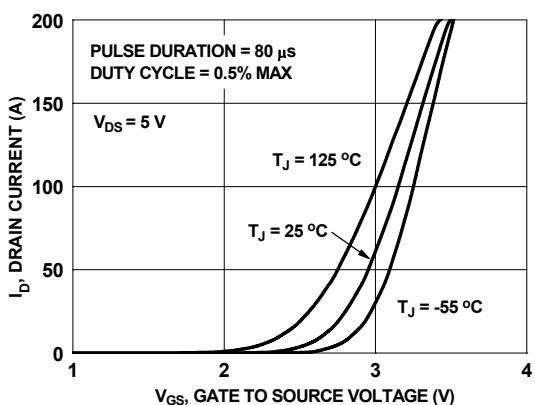


Figure 5. Transfer Characteristics

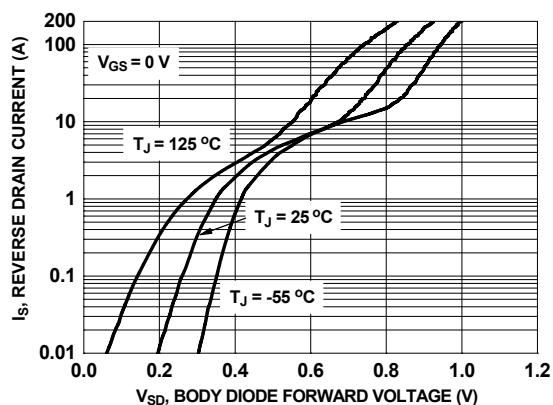


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

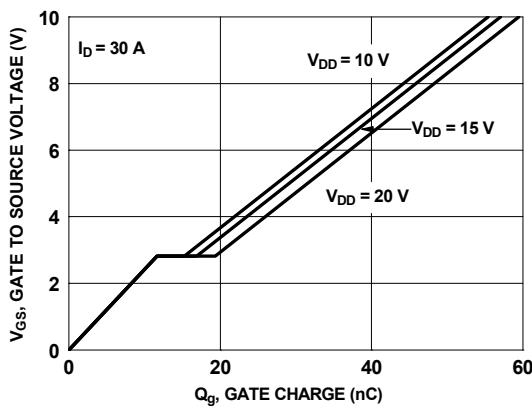


Figure 7. Gate Charge Characteristics

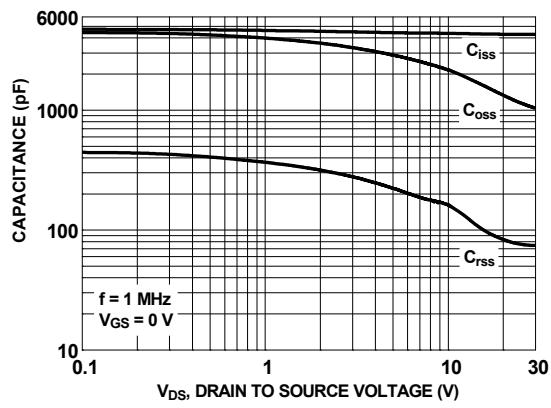


Figure 8. Capacitance vs Drain to Source Voltage

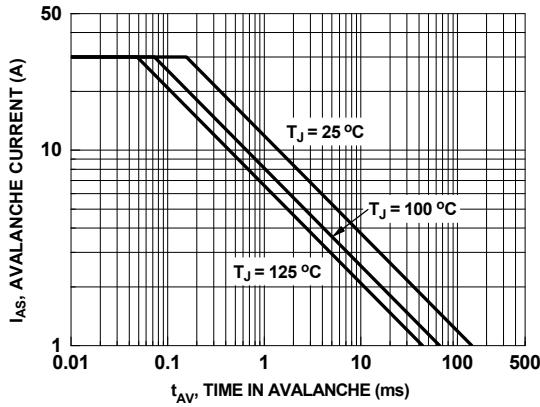


Figure 9. Unclamped Inductive Switching Capability

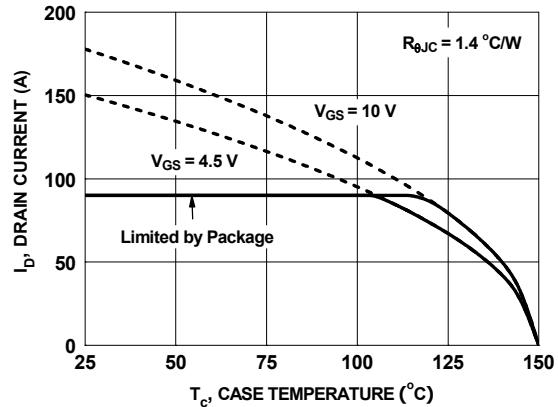


Figure 10. Maximum Continuous Drain Current vs Case Temperature

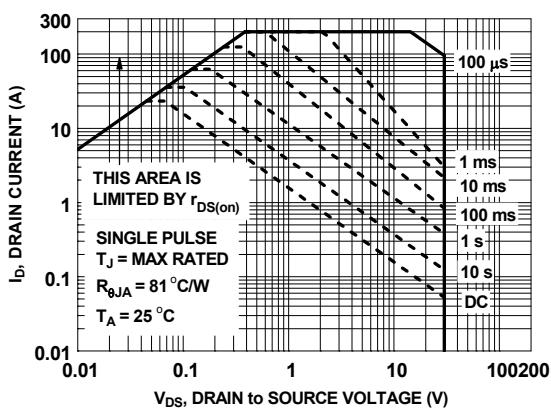


Figure 11. Forward Bias Safe Operating Area

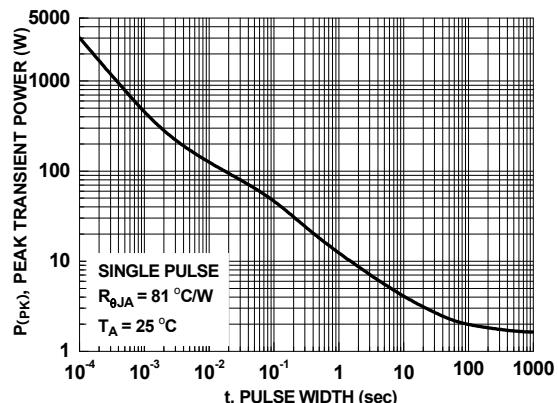


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

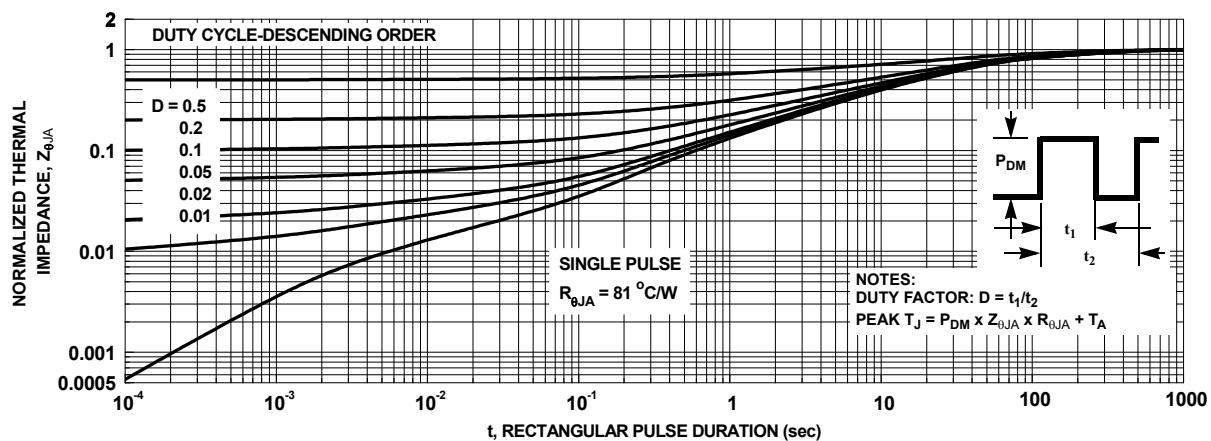


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET Schottky body diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS3006SDC.

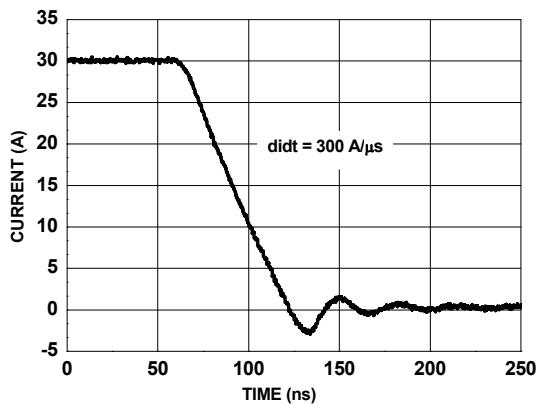


Figure 14. FDMS3006SDC SyncFET body diode reverse recovery characteristic

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

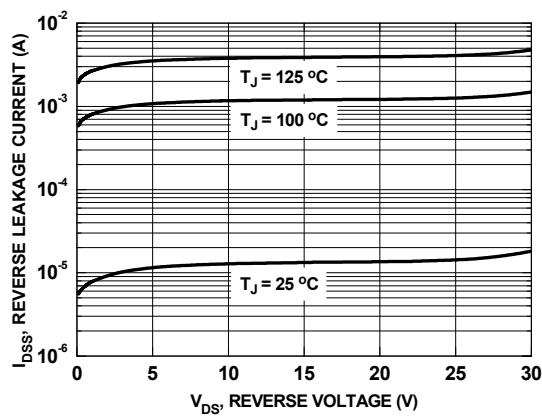
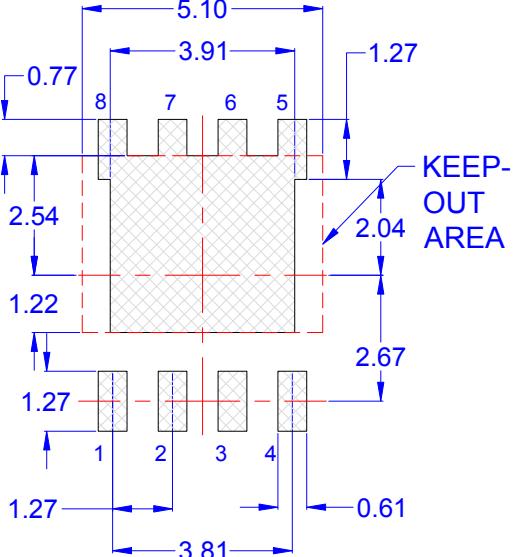
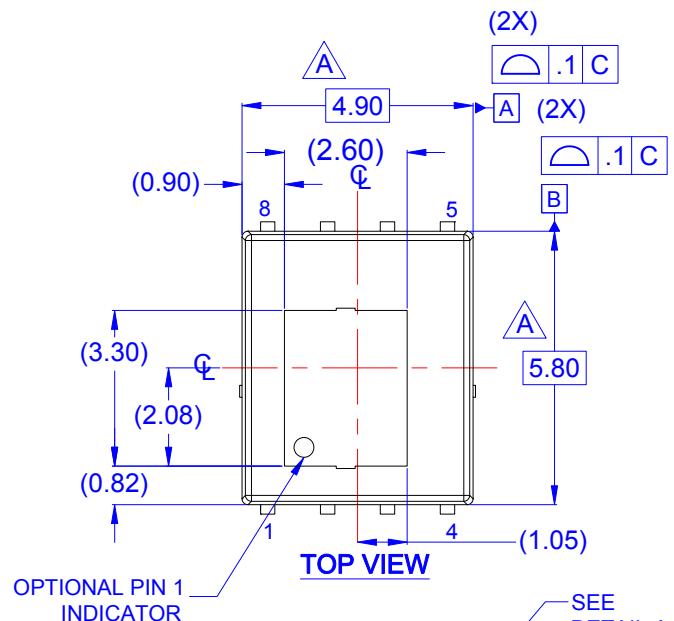
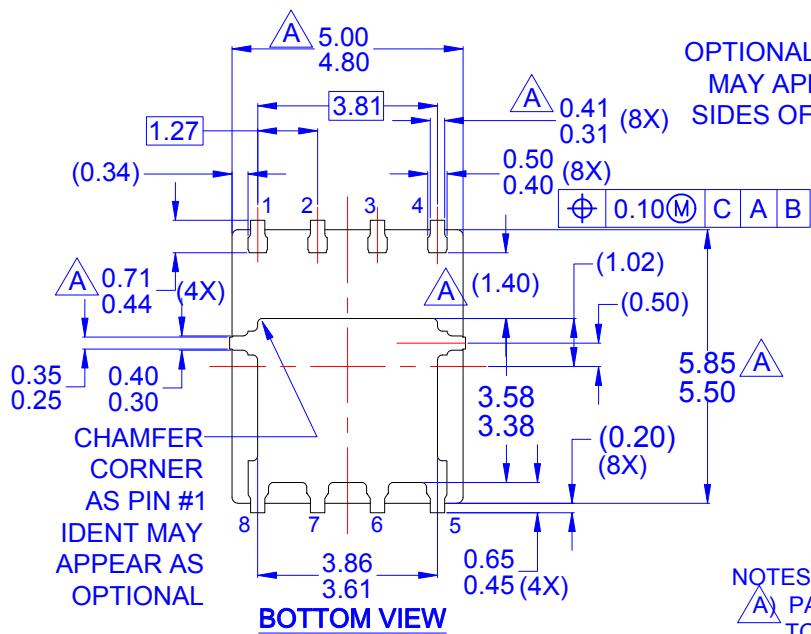


Figure 15. SyncFET body diode reverse leakage versus drain-source voltage

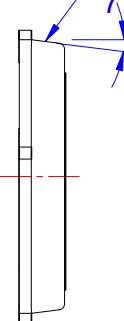


FRONT VIEW

DETAIL A



OPTIONAL DRAFT ANGLE
MAY APPEAR ON FOUR
SIDES OF THE PACKAGE -



SIDE VIEW

NOTES:

- A) PACKAGE IS NOT FULLY COMPLIANT TO JEDEC MO-240, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E) IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
- F) DRAWING FILE NAME: PQFN08DREV4



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